

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings of claims in the present application.

Listing of Claims:

1. (Original) A semiconductor device comprising:
 - a semiconductor substrate having a channel region and an impurity region disposed at both sides of the channel region;
 - a first polysilicon layer disposed on a surface of the channel region;
 - a gate oxide film disposed between the first polysilicon layer and the surface of the channel region and extending laterally to have a width larger than that of the first polysilicon film, wherein a thickness of the edge of the gate oxide film is larger than that of the center portion thereof so as to surround side walls of the first polysilicon film;
 - a gate electrode, disposed on the first polysilicon film, comprising a metal layer and a second polysilicon layer surrounding the metal layer; and
 - an insulating film spacer disposed on both sides of the gate electrode.
2. (Currently Amended) A semiconductor device according to ~~the~~ claim 1, wherein the gate oxide film is a thermal oxide film.
3. (Currently Amended) A semiconductor device according to ~~the~~ claim 1, wherein the gate oxide film consists of SiO₂, SiN or Ta₂O₅.
4. (Currently Amended) A semiconductor device according to ~~the~~ claim 1, wherein the impurity region comprises a low concentration impurity region extending from the both ends of the

channel region and a high concentration impurity region extending from both sides of ~~the~~ a low concentration impurity region.

5. (Currently Amended) A semiconductor device according to ~~the~~ claim 4, wherein the low and the high concentration impurity regions are ion-implanted with ~~a~~ an ion having a first conductive type, and the channel region is ion-implanted with ~~a~~ an ion having a second conductive type, the first conductive type being an opposite conductive type to the second conductive type.

6. (Currently Amended) A semiconductor device according to ~~the~~ claim 1, wherein the metal layer consists of W or Al.

Claims 7-14 (Cancelled).